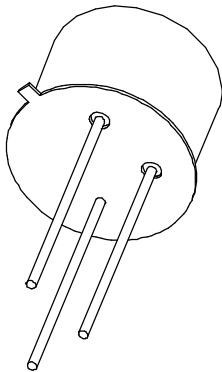


DATA SHEET



2N2219; 2N2219A **NPN switching transistors**

Product specification
Supersedes data of 1997 May 07
File under Discrete Semiconductors, SC04

1997 Sep 03

NPN switching transistors

2N2219; 2N2219A

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- High-speed switching
- DC and VHF/UHF amplification, for 2N2219 only.

DESCRIPTION

NPN switching transistor in a TO-39 metal package.
PNP complement: 2N2905 and 2N2905A.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case

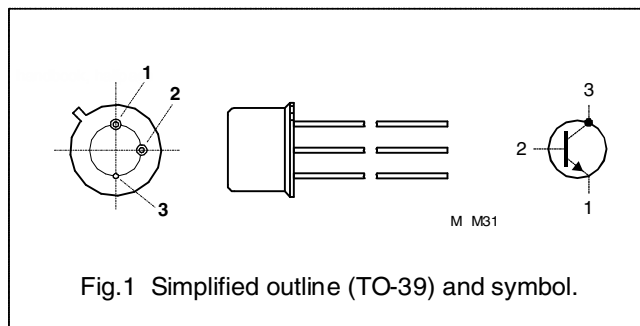


Fig.1 Simplified outline (TO-39) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	2N2219		—	60	V
	2N2219A		—	75	V
V_{CEO}	collector-emitter voltage	open base			
	2N2219		—	30	V
	2N2219A		—	40	V
I_C	collector current (DC)		—	800	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$	—	800	mW
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	—	
f_T	transition frequency	$I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$			
	2N2219		250	—	MHz
	2N2219A		300	—	MHz
t_{off}	turn-off time	$I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA}; I_{Boff} = -15\text{ mA}$	—	250	ns

NPN switching transistors

2N2219; 2N2219A

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	2N2219		–	60	V
	2N2219A		–	75	V
V _{CEO}	collector-emitter voltage	open base	–	30	V
	2N2219A	open base; I _C ≤ 500 mA	–	40	V
V _{EBO}	emitter-base voltage	open collector			
	2N2219		–	5	V
	2N2219A		–	6	V
I _C	collector current (DC)		–	800	mA
I _{CM}	peak collector current		–	800	mA
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	800	mW
		T _{case} ≤ 25 °C	–	3	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	200	°C
T _{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air	190	K/W
R _{th j-c}	thermal resistance from junction to case		50	K/W

NPN switching transistors

2N2219; 2N2219A

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current 2N2219	$I_E = 0$; $V_{CB} = 50\text{ V}$	–	10	nA
		$I_E = 0$; $V_{CB} = 50\text{ V}$; $T_{amb} = 150\text{ }^{\circ}\text{C}$	–	10	μA
I_{CBO}	collector cut-off current 2N2219A	$I_E = 0$; $V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0$; $V_{CB} = 60\text{ V}$; $T_{amb} = 150\text{ }^{\circ}\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 3\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}$; $V_{CE} = 10\text{ V}$	35	–	
h_{FE}	DC current gain	$I_C = 1\text{ mA}$; $V_{CE} = 10\text{ V}$	50	–	
h_{FE}	DC current gain	$I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$	75	–	
h_{FE}	DC current gain 2N2219A	$I_C = 10\text{ mA}$; $V_{CE} = 10\text{ V}$; $T_{amb} = -55\text{ }^{\circ}\text{C}$	35	–	
h_{FE}	DC current gain	$I_C = 150\text{ mA}$; $V_{CE} = 1\text{ V}$; note 1	50	–	
h_{FE}	DC current gain	$I_C = 150\text{ mA}$; $V_{CE} = 10\text{ V}$; note 1	100	300	
h_{FE}	DC current gain 2N2219 2N2219A	$I_C = 500\text{ mA}$; $V_{CE} = 10\text{ V}$; note 1	30 40	– –	
V_{CEsat}	collector-emitter saturation voltage 2N2219 2N2219A	$I_C = 150\text{ mA}$; $I_B = 15\text{ mA}$; note 1	–	400	mV
			–	300	mV
V_{CEsat}	collector-emitter saturation voltage 2N2219 2N2219A	$I_C = 500\text{ mA}$; $I_B = 50\text{ mA}$; note 1	–	1.6	V
			–	1	V
V_{BEsat}	base-emitter saturation voltage 2N2219 2N2219A	$I_C = 150\text{ mA}$; $I_B = 15\text{ mA}$; note 1	–	1.3	V
			0.6	1.2	V
V_{BEsat}	base-emitter saturation voltage 2N2219 2N2219A	$I_C = 500\text{ mA}$; $I_B = 50\text{ mA}$; note 1	–	2.6	V
			–	2	V
C_c	collector capacitance	$I_E = I_e = 0$; $V_{CB} = 10\text{ V}$	–	8	pF
C_e	emitter capacitance 2N2219A	$I_C = I_c = 0$; $V_{EB} = 500\text{ mV}$	–	25	pF
f_T	transition frequency 2N2219 2N2219A	$I_C = 20\text{ mA}$; $V_{CE} = 20\text{ V}$; $f = 100\text{ MHz}$;	250	–	MHz
			300	–	MHz
F	noise figure 2N2219A	$I_C = 0.2\text{ mA}$; $V_{CE} = 5\text{ V}$; $R_S = 2\text{ k}\Omega$; $f = 1\text{ kHz}$; $B = 200\text{ Hz}$	–	4	dB

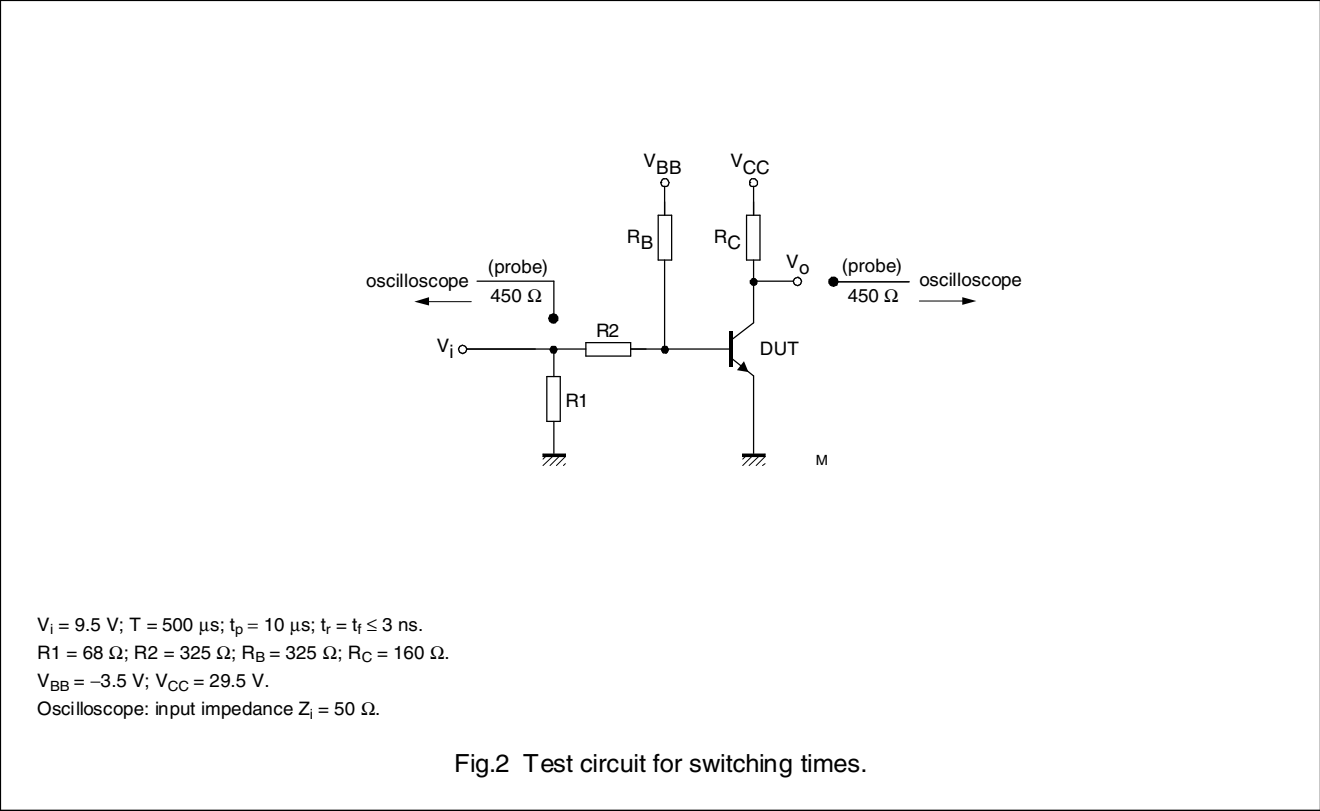
NPN switching transistors

2N2219; 2N2219A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Switching times (between 10% and 90% levels) for type 2N2219A; see Fig.2					
t _{on}	turn-on time	I _C on = 150 mA; I _B on = 15 mA; I _B off = -15 mA	—	35	ns
t _d	delay time		—	15	ns
t _r	rise time		—	20	ns
t _{off}	turn-off time		—	250	ns
t _s	storage time		—	200	ns
t _f	fall time		—	60	ns

Note

1. Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.



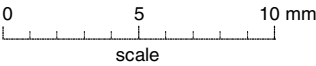
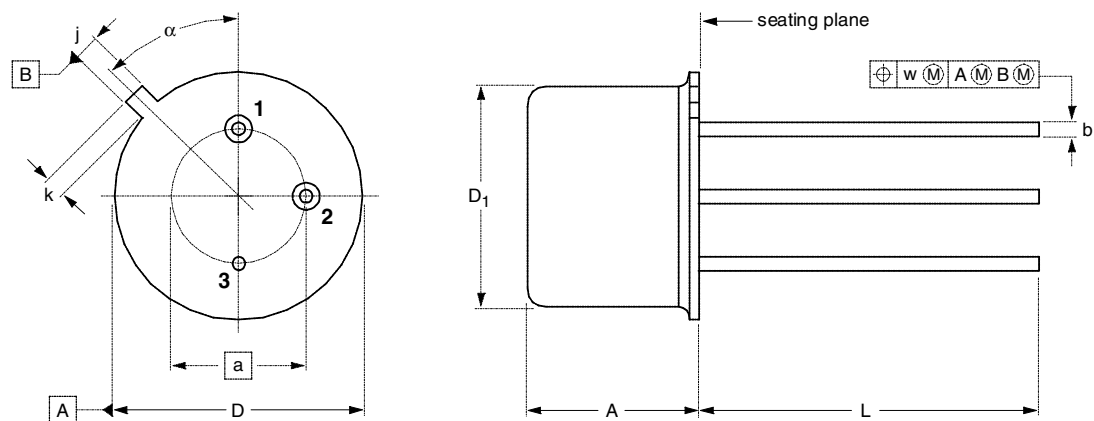
NPN switching transistors

2N2219; 2N2219A

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D ₁	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

NPN switching transistors2N2219; 2N2219A

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 34 Waterloo Road, NORTH RYDE, NSW 2113,
Tel. +61 2 9805 4455, Fax. +61 2 9805 4466

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213, Tel. +43 160 1010,
Fax. +43 160 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 200 733, Fax. +375 172 200 773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoprojekt, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 689 211, Fax. +359 2 689 102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381

China Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Prags Boulevard 80, PB 1919, DK-2300 COPENHAGEN S,
Tel. +45 32 88 2636, Fax. +45 31 57 0044

Finland: Sinikallontie 3, FIN-02630 ESPOO,
Tel. +358 9 615800, Fax. +358 9 61580920

France: 4 Rue du Port-aux-Vins, BP317, 92156 SURESNES Cedex,
Tel. +33 1 40 99 6161, Fax. +33 1 40 99 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 23 53 60, Fax. +49 40 23 536 300

Greece: No. 15, 25th March Street, GR 17778 TAVROS/ATHENS,
Tel. +30 1 4894 339/239, Fax. +30 1 4814 240

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: see Singapore

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Piazza IV Novembre 3,
20124 MILANO, Tel. +39 2 6752 2531, Fax. +39 2 6752 2557

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108,
Tel. +81 3 3740 5130, Fax. +81 3 3740 5077

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Ul. Lukiska 10, PL 04-123 WARSZAWA,
Tel. +48 22 612 2831, Fax. +48 22 612 2327

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 1231,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

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South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 7430 Johannesburg 2000,
Tel. +27 11 470 5911, Fax. +27 11 470 5494

South America: Rua do Rocio 220, 5th floor, Suite 51,
04552-903 São Paulo, SÃO PAULO - SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 829 1849

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 3 301 6312, Fax. +34 3 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 632 2000, Fax. +46 8 632 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2686, Fax. +41 1 481 7730

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2865, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Talatpasa Cad. No. 5, 80640 GÜLTEPE/ISTANBUL,
Tel. +90 212 279 2770, Fax. +90 212 282 6707

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 181 730 5000, Fax. +44 181 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381

Uruguay: see South America

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Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 625 344, Fax. +381 11 635 777

For all other countries apply to: Philips Semiconductors, Marketing & Sales Communications,
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